



Product Change Notification



Product Group: Dale Resistors / February 28, 2020 / PCN-DR-00007-2020 Rev 0

CSC - Thick Film Resistor Networks, Single-In-Line, Conformal Coated SIP, Manufacturing Location Change

DESCRIPTION OF CHANGE: Change in manufacturing location from Asia to Mexico. Product coating color will change from black to gold.

CLASSIFICATION OF CHANGE: Assembly site / Form, Fit, Function

REASON FOR CHANGE: Change COO from Asia to Mexico.

EXPECTED INFLUENCE ON QUALITY/RELIABILITY/PERFORMANCE: There will be no effect on quality, reliability or performance.

PRODUCT CATEGORY: Resistors, Discrete

PART NUMBERS/SERIES/FAMILIES AFFECTED: CSC-Thick Film Resistor Networks, Single-In-Line, Conformal Coated SIP

VISHAY BRAND(s): Vishay Dale

TIME SCHEDULE:

Start Shipment Date:	Approximately July 1, 2020
Last Time Buy Date:	Not Applicable
Last Time Shipment Date:	Not Applicable

SAMPLE AVAILABILITY: Not Applicable

PRODUCT IDENTIFICATION: Not Applicable

QUALIFICATION DATA: No qualification data will be available.

This PCN is considered approved, without further notification, unless we receive specific customer concerns before May 4, 2020 or as specified by contract.

ISSUED BY: Neal Kratochvil, Sr. Product Marketing Engineer, neal.kratochvil@vishay.com

For further information, please contact your regional Vishay office.

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Procedure #